Erratum to: Simulation of InGaN/GaN light-emitting diodes with patterned sapphire substrate

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In our published manuscript, the simulated results for PSS case A in Fig. 4 were incorrect. The correct results can be seen in the following figure:

The online version of the original article can be found under doi:[10.1007/s11082-013-9675-3](https://doi.org/10.1007/s11082-013-9675-3).

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